



#### Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	$I_D$
-100V	145mΩ@-10V	-12A

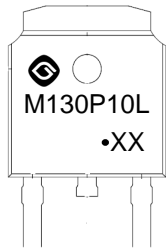
#### Feature

- Trench Technology Power MOSFET
- Low  $R_{DS(ON)}$
- Low Gate Charge
- Low Gate Resistance
- 100% UIS Tested

#### Application

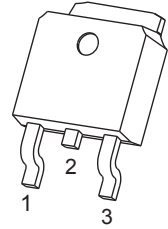
- Power Switching Application

#### MARKING:



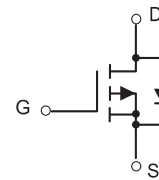
M130P10L = Device Code  
XX = Date Code  
Solid Dot = Green Indicator

TO-252-2L



1. GATE
2. DRAIN
3. SOURCE

Schematic diagram



#### ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit	
Drain - Source Voltage	$V_{DS}$	-100	V	
Gate - Source Voltage	$V_{GS}$	$\pm 20$	V	
Continuous Drain Current <sup>1</sup>	$T_C = 25^\circ\text{C}$	$I_D$	-12	A
	$T_C = 100^\circ\text{C}$	$I_D$	-9	A
Pulsed Drain Current <sup>2</sup>	$I_{DM}$	-48	A	
Single Pulsed Avalanche Current <sup>3</sup>	$I_{AS}$	-15	A	
Single Pulsed Avalanche Energy <sup>3</sup>	$E_{AS}$	56.3	mJ	
Power Dissipation <sup>5</sup>	$T_C = 25^\circ\text{C}$	$P_D$	33	W
Thermal Resistance from Junction to Ambient <sup>6</sup>	$R_{\theta JA}$	56	$^\circ\text{C}/\text{W}$	
Thermal Resistance from Junction to Case	$R_{\theta JC}$	3.75	$^\circ\text{C}/\text{W}$	
Junction Temperature	$T_J$	150	$^\circ\text{C}$	
Storage Temperature	$T_{STG}$	-55~ +150	$^\circ\text{C}$	

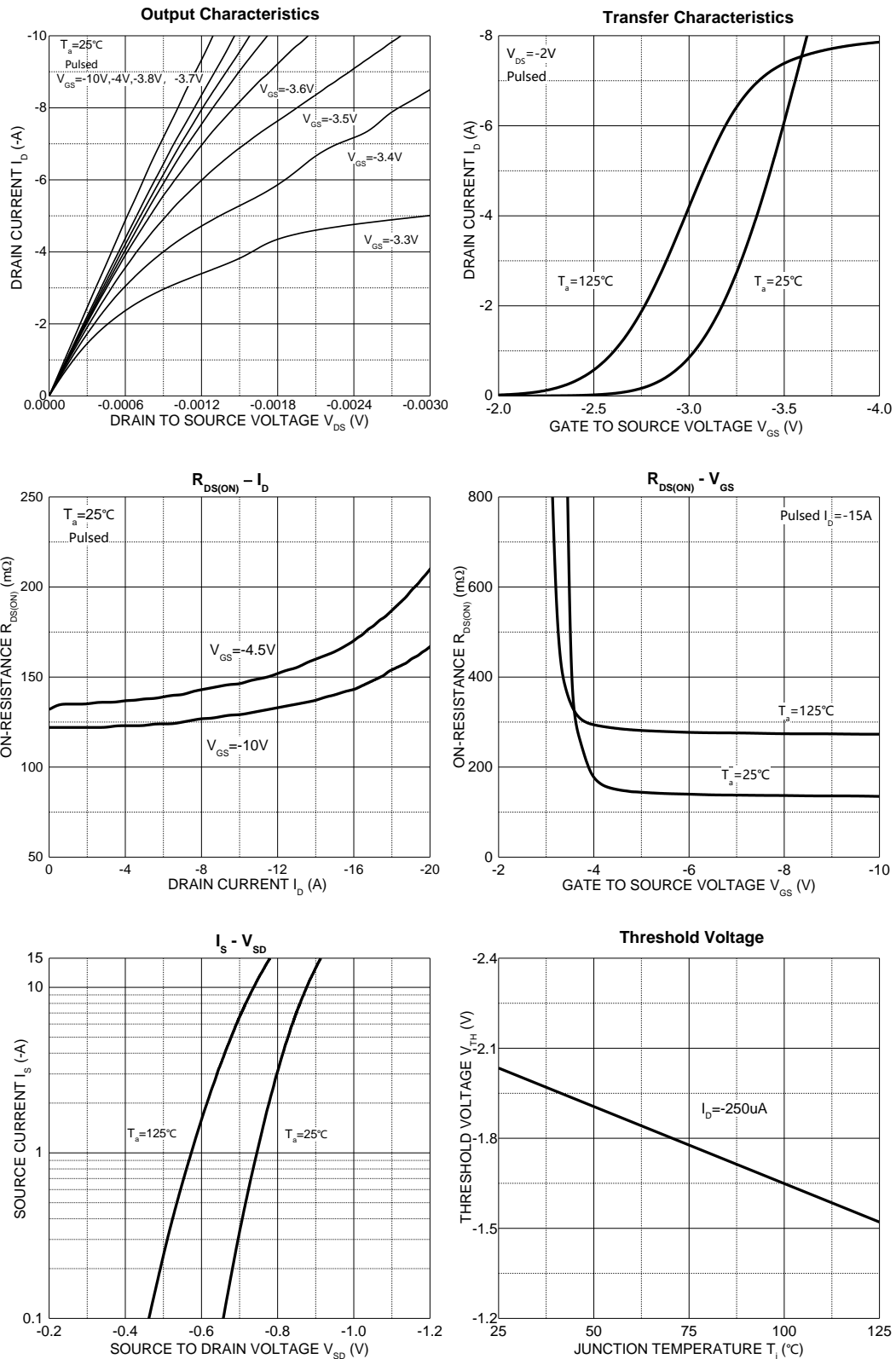
## MOSFET ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

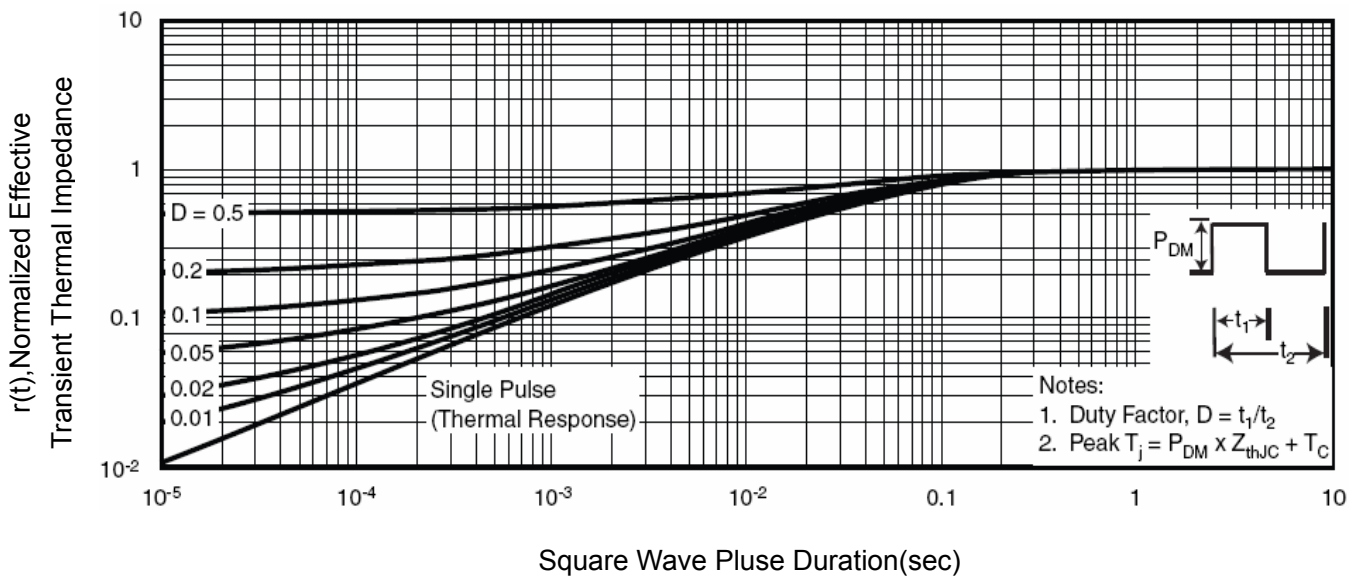
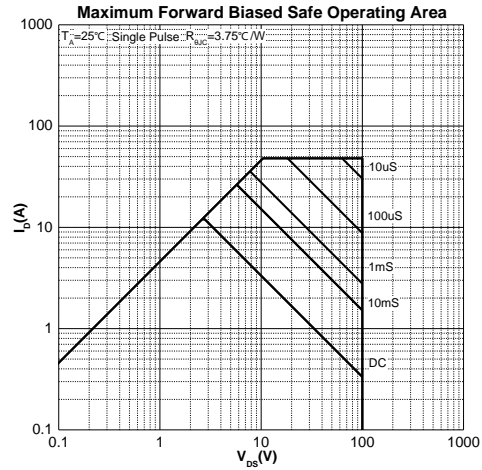
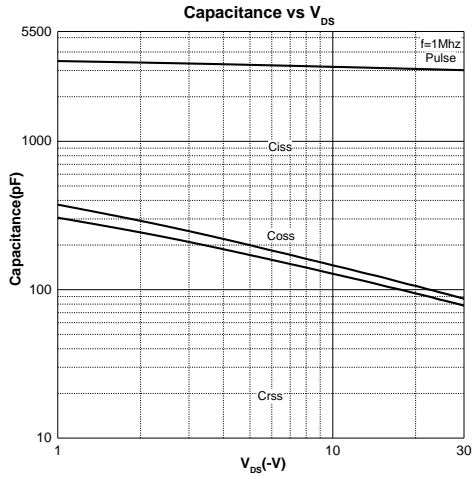
Parameter	Symbol	Test Condition	Min	Type	Max	Unit
<b>Off Characteristics</b>						
Drain - Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = -250\mu A$	-100			V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = -100V, V_{GS} = 0V$			1	$\mu A$
Gate - Body Leakage Current	$I_{GSS}$	$V_{GS} = \pm 20V, V_{DS} = 0V$			$\pm 100$	nA
<b>On Characteristics<sup>4</sup></b>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu A$	-1.0	-2.0	-3.0	V
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = -10V, I_D = -15A$		145	168	m $\Omega$
Forward Transconductance	$g_{FS}$	$V_{DS} = -5V, I_D = -5A$	12			S
<b>Dynamic Characteristics</b>						
Input Capacitance	$C_{iss}$	$V_{DS} = -45V, V_{GS} = 0V, f = 1MHz$		2926		pF
Output Capacitance	$C_{oss}$			72		
Reverse Transfer Capacitance	$C_{rss}$			66		
Gate Resistance	$R_g$	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$		9.1		$\Omega$
<b>Switching Characteristics</b>						
Total Gate Charge	$Q_g$	$V_{DS} = -55V, V_{GS} = -10V, I_D = -15A$		55		nC
Gate-Source Charge	$Q_{gs}$			10		
Gate-Drain Charge	$Q_{gd}$			11		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -50V, V_{GS} = -10V, I_D = -10A, R_G = 9.1\Omega$		11		ns
Turn-On Rise Time	$t_r$			50		
Turn-Off Delay Time	$t_{d(off)}$			24		
Turn-Off Fall Time	$t_f$			35		
<b>Source - Drain Diode Characteristics</b>						
Diode Forward Voltage <sup>4</sup>	$V_{SD}$	$V_{GS} = 0V, I_S = -10A$			-1.2	V
Diode Reverse Recovery Time	$t_{rr}$	$I_F = -10A, dI/dt = 500A/ms$		33		ns
Diode Reverse Recovery Charge	$Q_{rr}$	$I_F = -10A, dI/dt = 500A/ms$		45		nC

Notes :

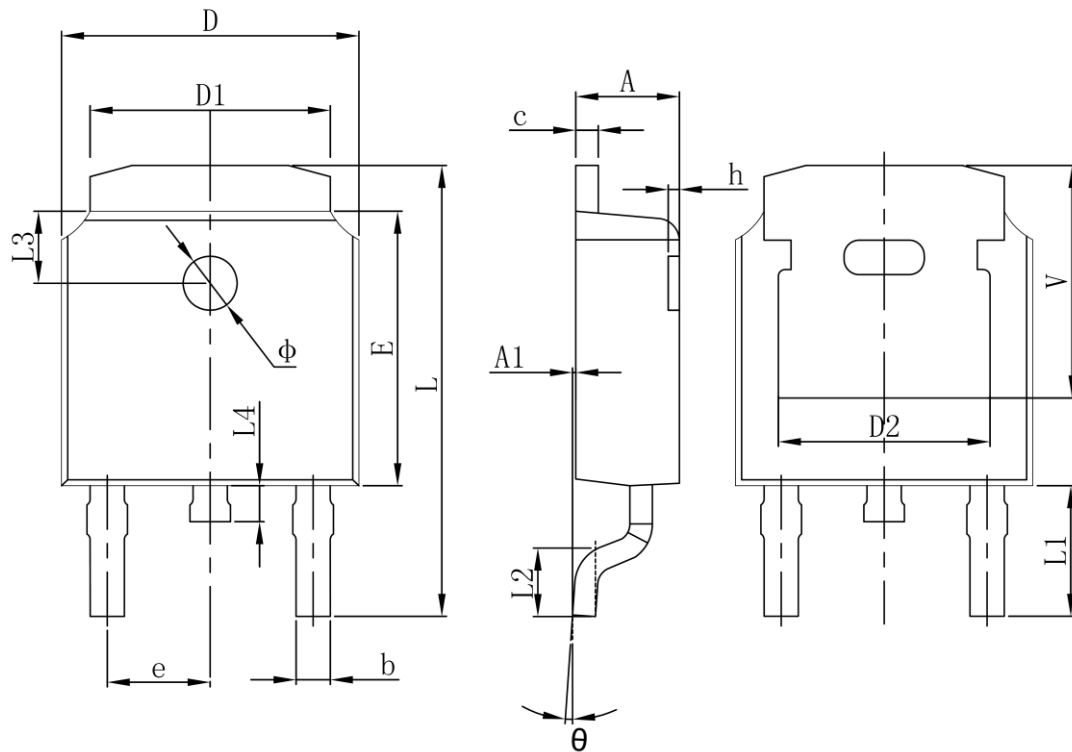
- 1.The maximum current rating is limited by package.And device mounted on a large heatsink
- 2.Pulse Test : Pulse Width  $\leq 10\mu s$ , duty cycle  $\leq 1\%$ .
- 3.EAS condition:  $V_{DD} = -50V, V_{GS} = -10V, L = 0.5mH, R_G = 25\Omega$  Starting  $T_J = 25^\circ C$ .
- 4.Pulse Test : Pulse Width  $\leq 300\mu s$ , duty cycle  $\leq 2\%$ .
- 5.The power dissipation  $P_D$  is limited by  $T_{J(MAX)} = 150^\circ C$ .And device mounted on a large heatsink
- 6.Device mounted on  $1in^2$  FR-4 board with 2oz. Copper, in a still air environment with  $T_A = 25^\circ C$ .

## Typical Characteristics





## TO-252-2L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.635	0.770	0.025	0.030
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830REF		0.190REF	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.712	10.312	0.382	0.406
L1	2.900REF		0.114REF	
L2	1.400	1.700	0.055	0.067
L3	1.600REF		0.063REF	
L4	0.600	1.000	0.024	0.039
φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.250REF		0.207REF	

**Attention:**

- GreenPower Electronics reserves the right to improve product design function and reliability without notice.
- Any and all semiconductor products have certain probability to fail or malfunction, which may result in personal injury, death or property damage. Customer are solely responsible for providing adequate safe measures when design their systems.
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